



/ Revised record

A	2018-12-18				
B	2019-4-20				
C	2019-7-24	1			
D	2021-10-26	4			

/ Descriptions

SOT-363 NPN+PNP

Double silicon NPN and PNP transistor in a SOT-363 Plastic Package.

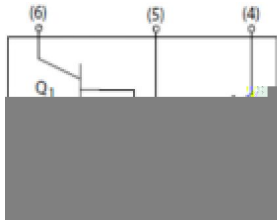
/ Features

Ideal for Low Power Amplification and Switching.HF Product.

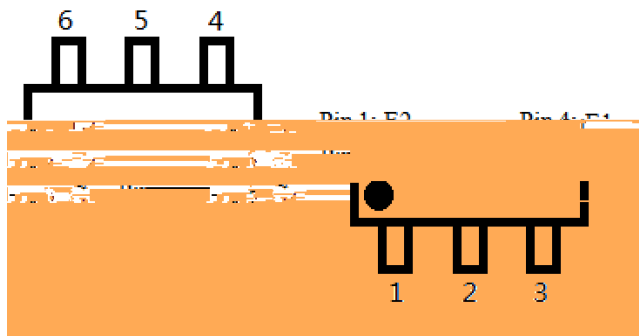
/ Applications

Power amplifier application.

/ Equivalent Circuit



/ Pinning



/ h_{FE} Classifications & Marking

See Marking Instructions.

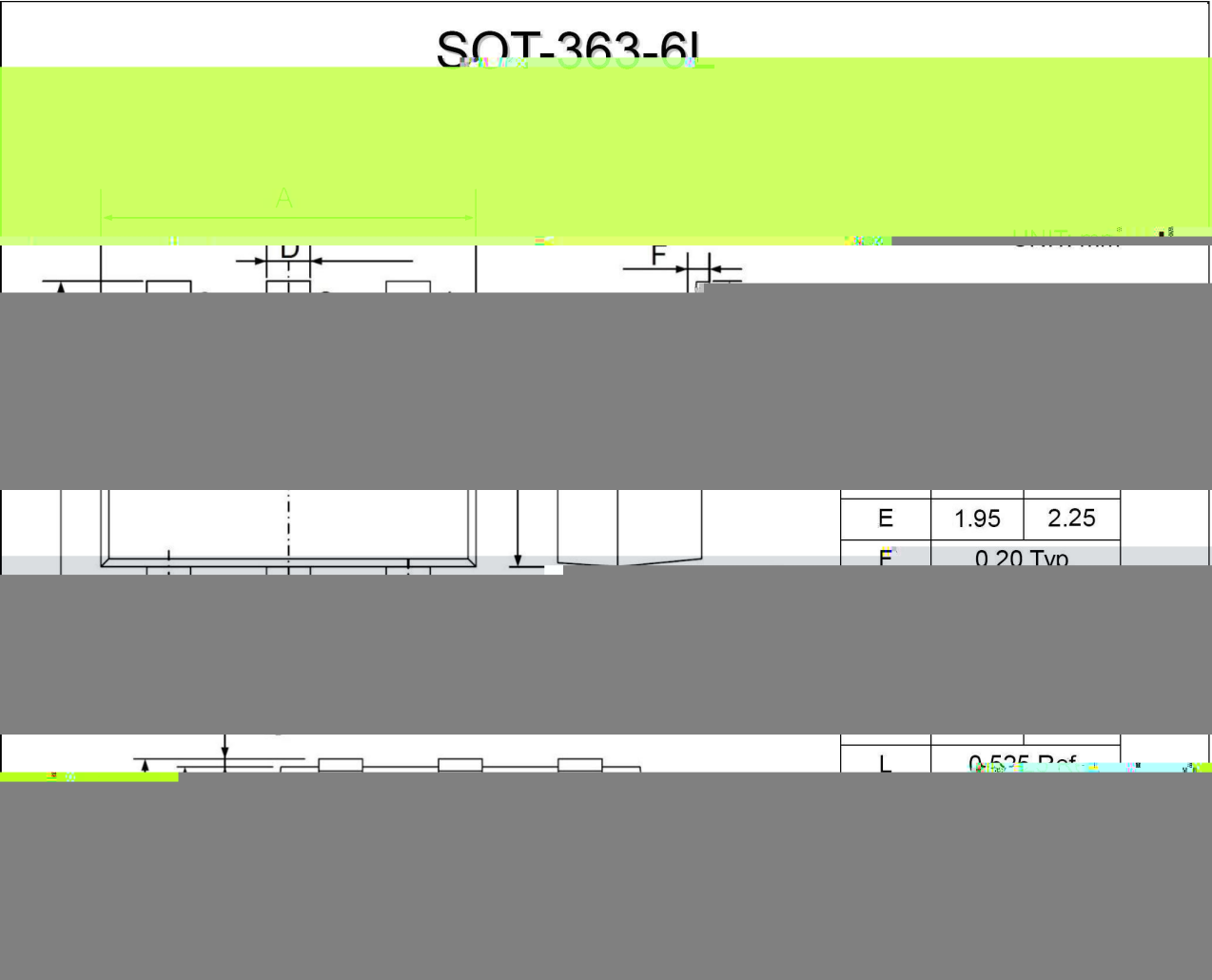
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Total Power Dissipation	P_d	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 150	

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CEO}	40	VE

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/ Package Dimensions



/ Marking Instructions

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Note:

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Product Type Code
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Note:

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|---|---------|-----------|--|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | 2 | 10°C/sec. | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type !	Units " # \$					Dimension " % & (unit ' mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box (	Outer Box)
SOT-363	3,000	10	30,000	6	180000	7" ×8	180×120×180	390×385×205